

DOCKET NO. 99-039

RESPONSE UNDER 37 C.F.R. 1.116 -  
EXPEDITED PROCEDURE  
EXAMINING GROUP 1765

#11  
12/21/02



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Sheldon Aronowitz, Valeriy Sukharev, John Haywood, James P. Kimball,  
Helmut Puchner, Ravindra Manohar Kapre, and Nicholas Eib

Appl. No. : 09/464,297

Filed: : December 15, 1999

Title : PROCESS FOR ETCHING A CONTROLLABLE THICKNESS OF  
OXIDE ON AN INTEGRATED CIRCUIT STRUCTURE ON A  
SEMICONDUCTOR SUBSTRATE USING NITROGEN PLASMA AND  
AN RF BIAS APPLIED TO THE SUBSTRATE

Grp./ A.U. : 1765

Examiner : Charlotte A. Brown

Docket No. : 99-039

CERTIFICATE OF MAILING	
I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231	
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RESPONSE TO FINAL REJECTION

Honorable Commissioner for Patents  
Washington, D.C. 20231

Date: December 12, 2002

Sir:

The following remarks are in response to the second Final Rejection mailed  
October 24, 2002, in this application.